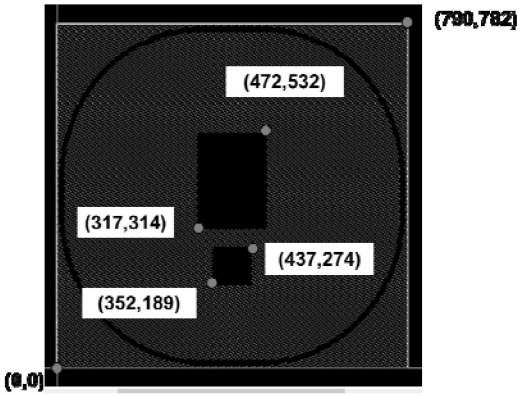
HSM200R600

600V N Channel MOSFETs Wafer Datasheet

Die Description

Parameter	Parameter	Rating	CHIP DRAWING
Die Size (with SL)	850 X 842	um^2	
Gate Pad Size	85 X 85		
Source Pad Size	155 X 218		
Scribe Line Size	60	um	
Wafer size	200	mm	
Wafer Thickness	10	mil	
Metallization	4um , Al-Cu (0.5%)		
Back Metallization	Ti/Ni/Ag , 1/3/10KA		
Gate Bond Wire	0.8 mil Au/Cu x 1		
Source Bond Wire	0.8 mil Au/Cu x 1		
Estimated Gross Die	40,000		

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	600V	V
V_{GSS}	Gate-Source Voltage	±30V	V
T_J	Operating Junction Temperature Range	-50 to 150℃	℃
T_{STG}	Storage Temperature Range	-50 to 150℃	℃

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	600	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=600V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=480V , V_{GS}=0V , T_J=85℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V , V_{DS}=0V	---	---	±100	nA
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=0.2A	---	120	200	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.5	2.4	3.5	V

Note：1. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
2. RDSON calculated by SOT23 Package Type